



PMV130E NEA

40 V, N-channel Trench MOSFET

12 June 2014

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- 1 kV ESD protected
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	-	40	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	2.1	A
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 1.5\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	95	120	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

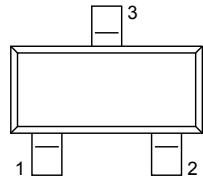
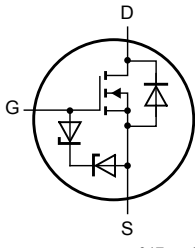


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		
	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV130ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code
PMV130ENEA	%JX

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$		-	40	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	2.1	A
		$V_{GS} = 10\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	1.3	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ °C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	8	A
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$T_{j(\text{init})} = 25\text{ °C}; I_D = 0.26\text{ A}; \text{DUT in avalanche (unclamped)}$		-	5.8	mJ
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	460	mW
			[1]	-	833	mW
		$T_{sp} = 25\text{ °C}$		-	5000	mW
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	$T_{amb} = 25\text{ °C}$	[1]	-	0.8	A
ESD maximum rating						
V_{ESD}	electrostatic discharge voltage	HBM	[3]	-	1000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .
- [2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

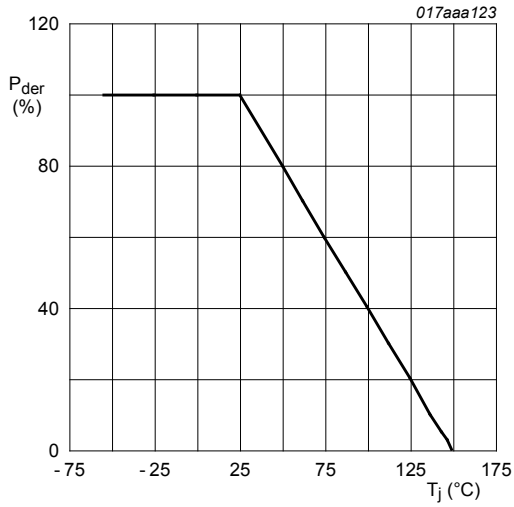


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

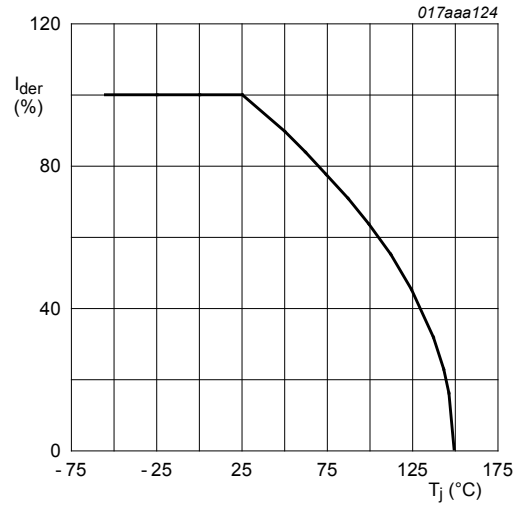
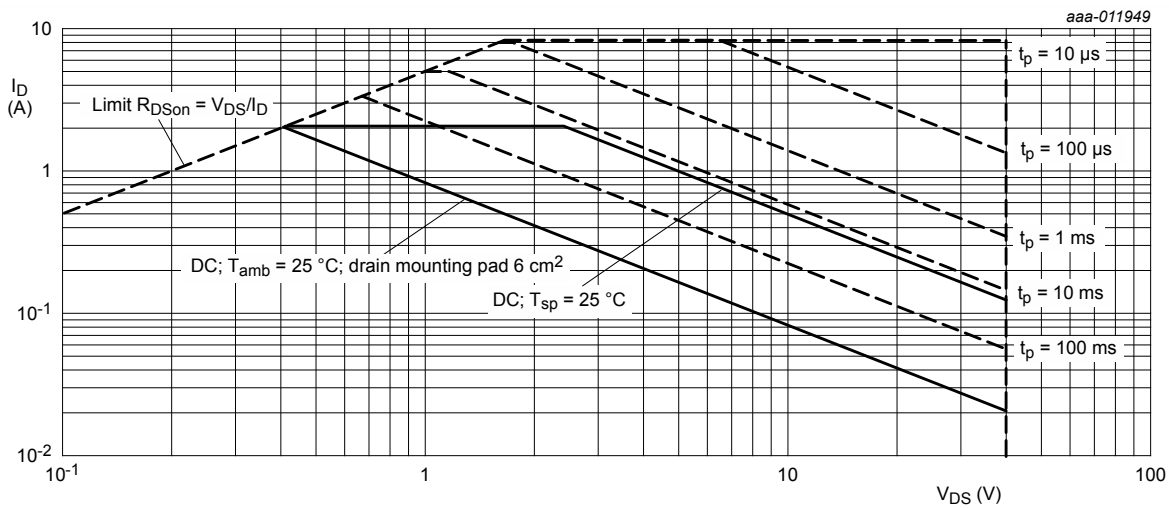


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	235	270	K/W
			[2]	-	125	150	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	20	25	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

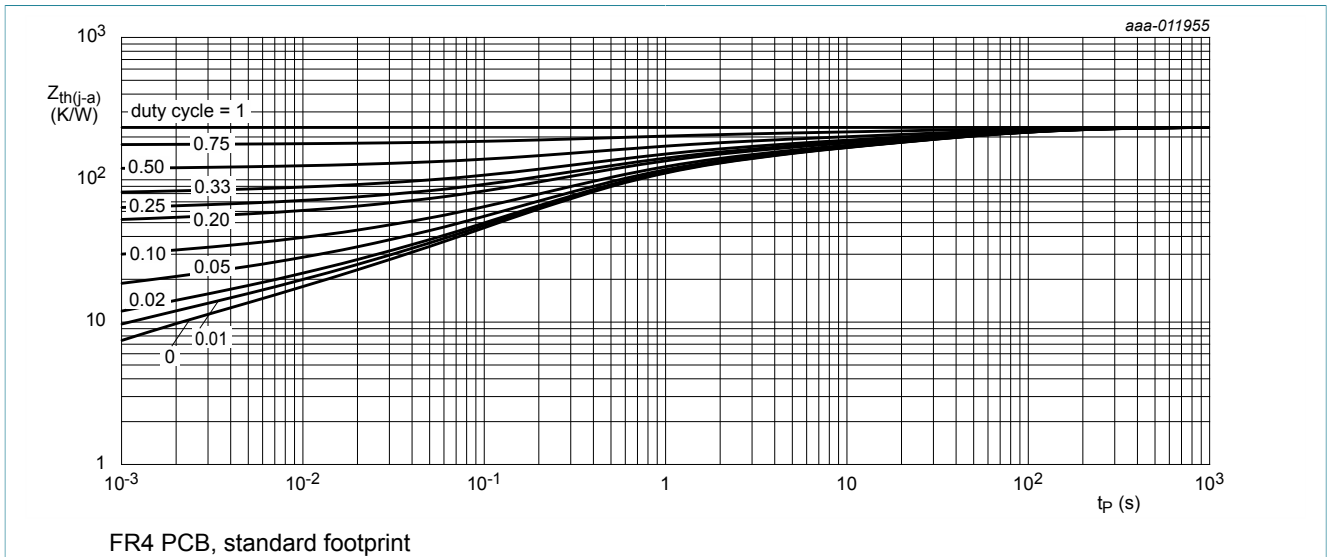


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

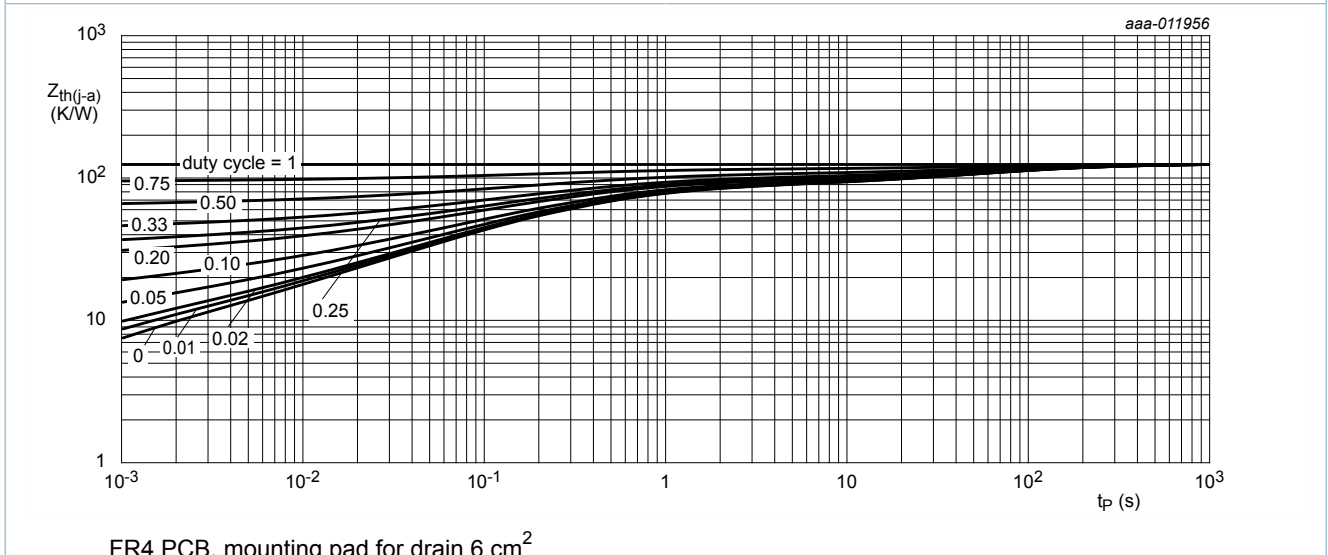


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	40	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1	1.6	2.5	V
I_{DSS}	drain leakage current	$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 40 V; V_{GS} = 0 V; T_j = 150 \text{ }^\circ C$	-	-	20	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	μA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 1.5 A; T_j = 25 \text{ }^\circ C$	-	95	120	m Ω
		$V_{GS} = 10 V; I_D = 1.5 A; T_j = 150 \text{ }^\circ C$	-	160	200	m Ω
		$V_{GS} = 4.5 V; I_D = 1 A; T_j = 25 \text{ }^\circ C$	-	120	160	m Ω
g_{fs}	forward transconductance	$V_{DS} = 10 V; I_D = 2 A; T_j = 25 \text{ }^\circ C$	-	4.5	-	S
R_G	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	-	21	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 20 V; I_D = 1.5 A; V_{GS} = 10 V; T_j = 25 \text{ }^\circ C$	-	2.4	3.6	nC
Q_{GS}	gate-source charge		-	0.3	-	nC
Q_{GD}	gate-drain charge		-	0.4	-	nC
C_{iss}	input capacitance	$V_{DS} = 20 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	113	170	pF
C_{oss}	output capacitance		-	27	-	pF
C_{rss}	reverse transfer capacitance		-	14	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 20 V; I_D = 1.5 A; V_{GS} = 10 V; R_{G(ext)} = 13 \text{ } \Omega; T_j = 25 \text{ }^\circ C$	-	6	9	ns
t_r	rise time		-	8	-	ns
$t_{d(off)}$	turn-off delay time		-	11	17	ns
t_f	fall time		-	3	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 0.8 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.8	1.2	V

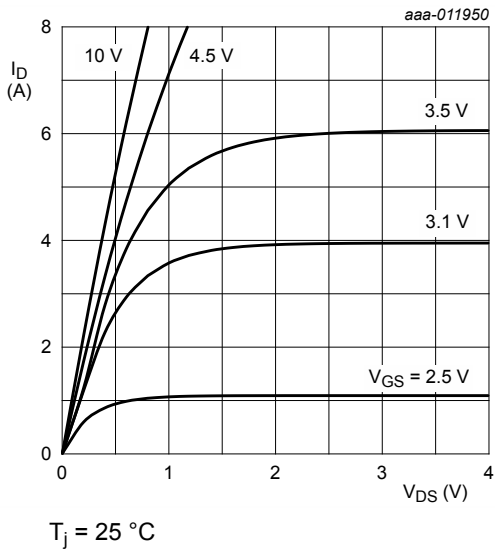


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

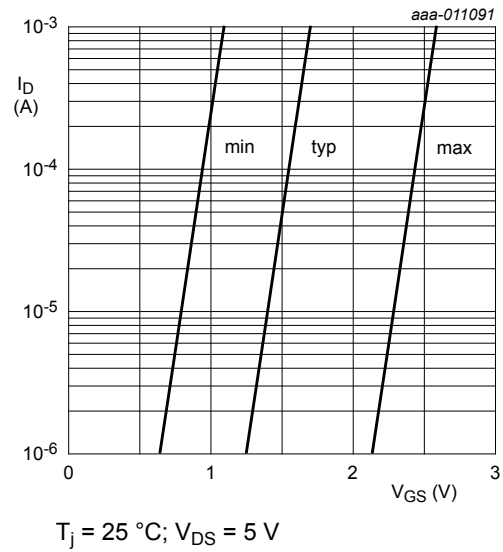


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

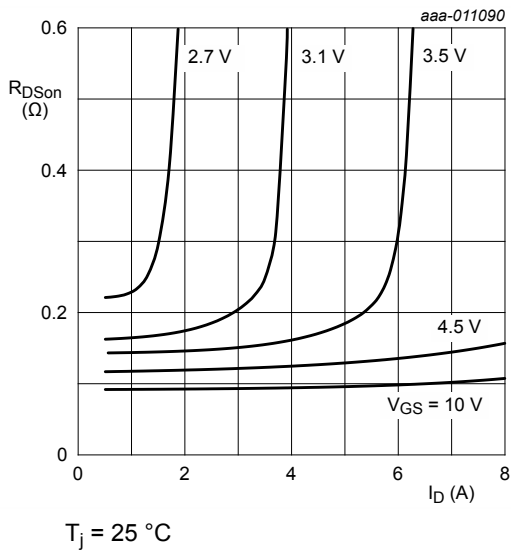


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

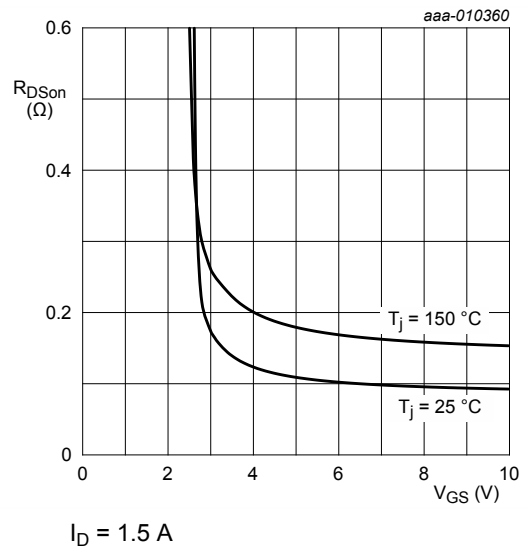
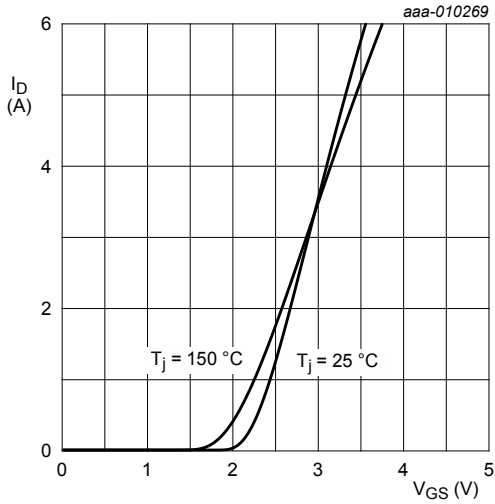


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

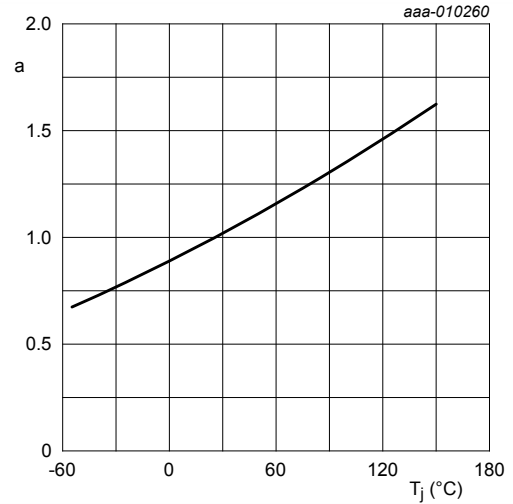
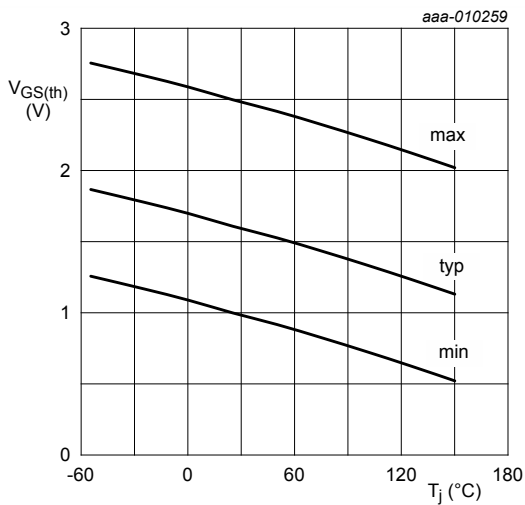


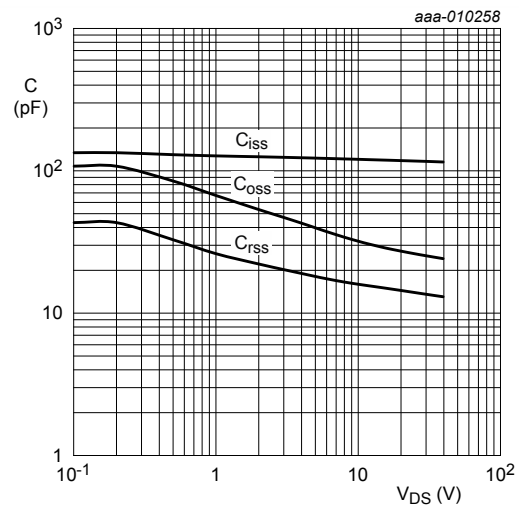
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



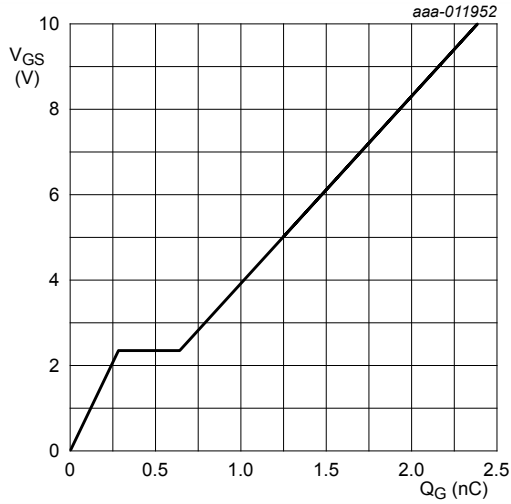
$$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 1.5 \text{ A}; V_{DS} = 20 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

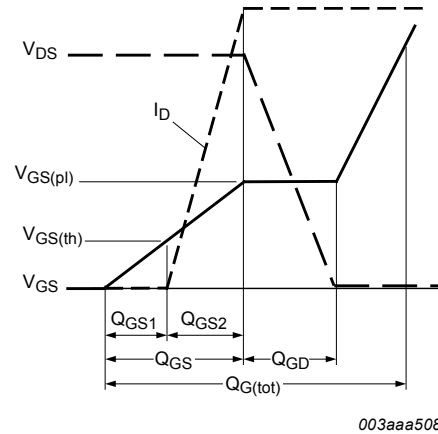
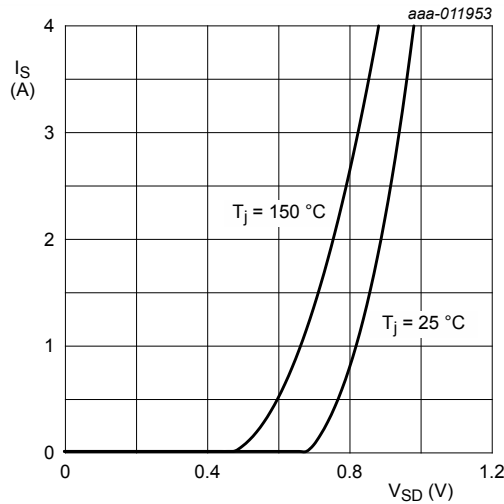


Fig. 15. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

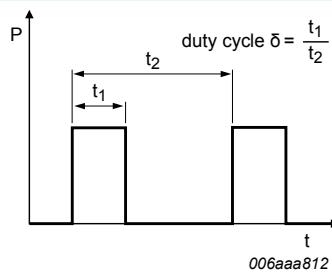


Fig. 17. Duty cycle definition

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

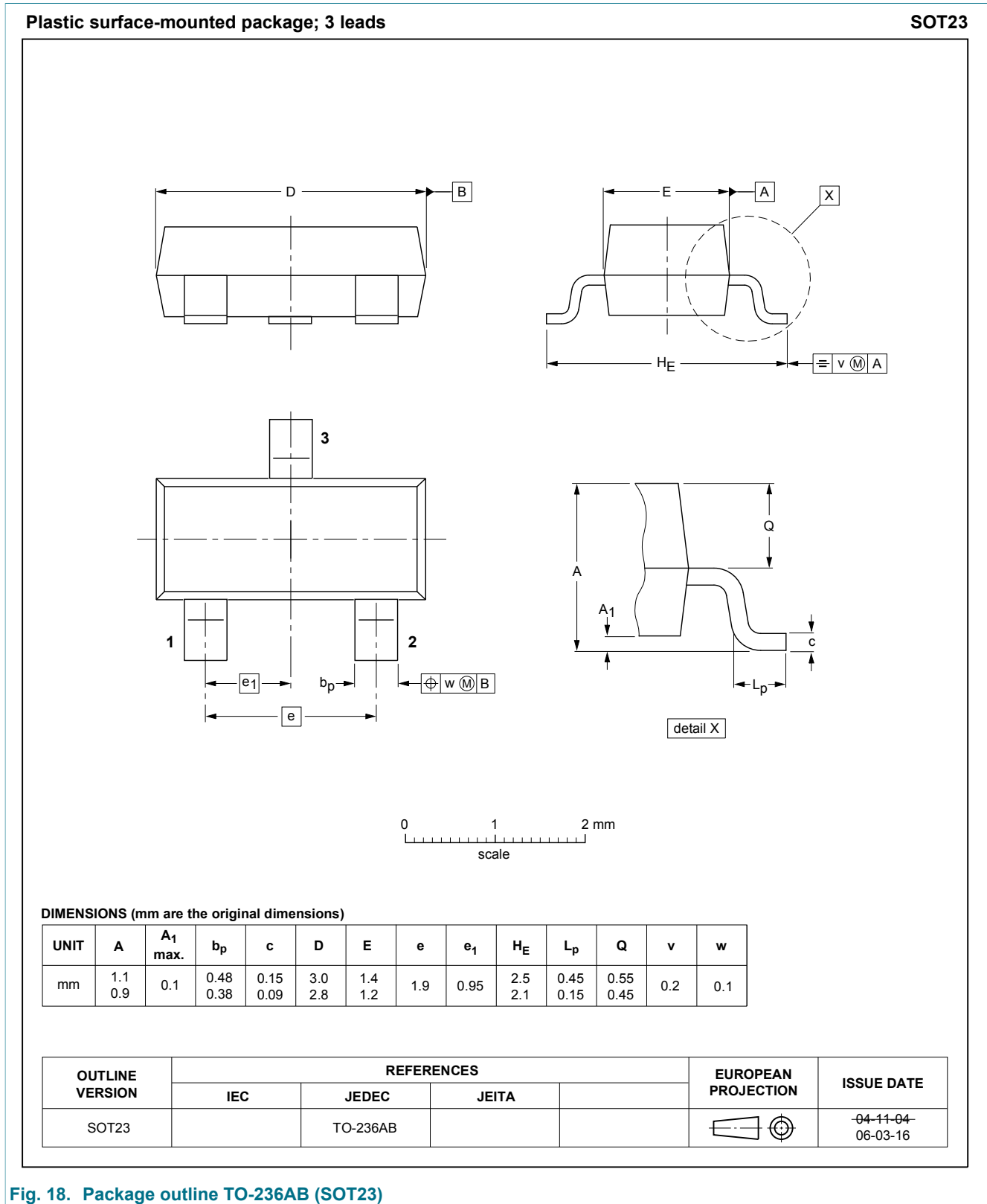


Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering

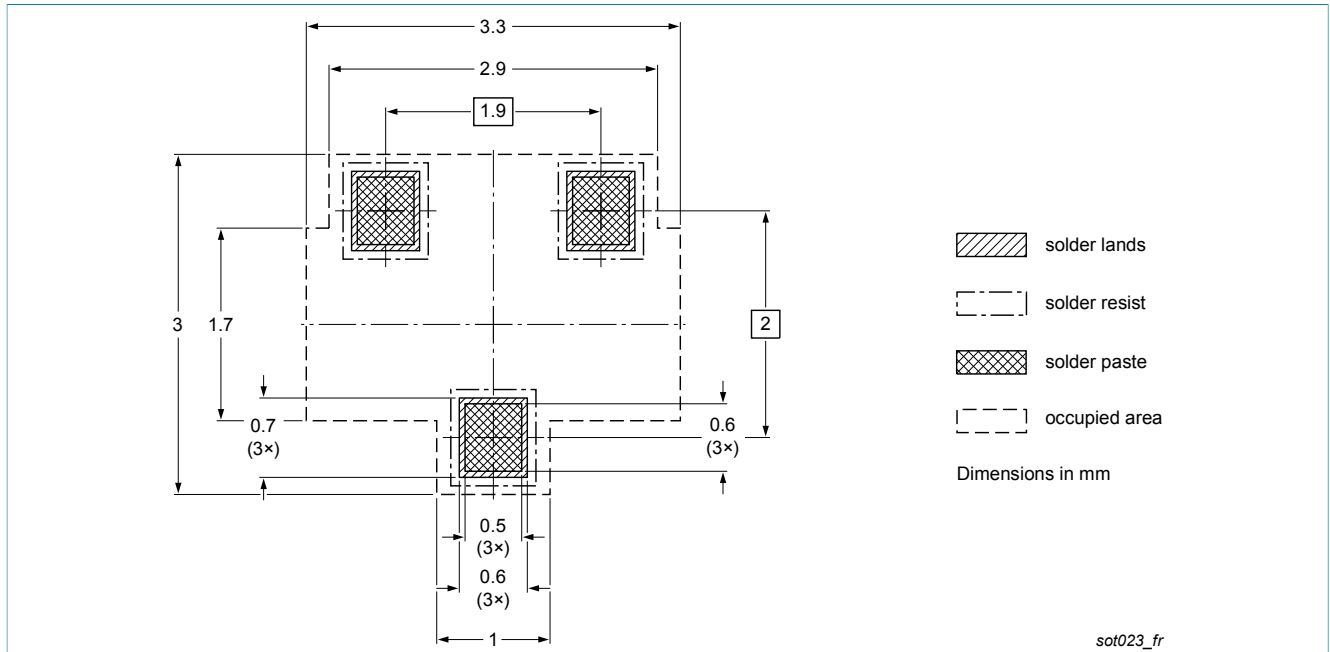


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

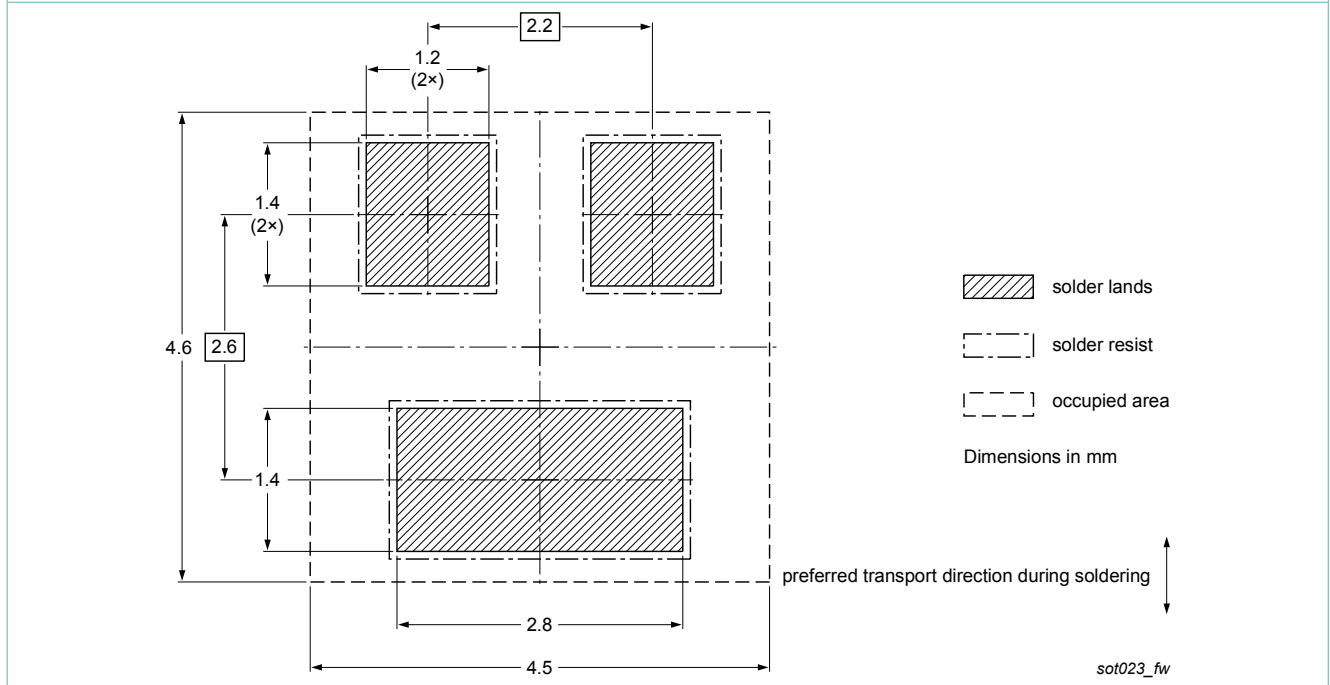


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV130ENEA v.2	20140612	Product data sheet	-	PMV130ENEA v.1
Modifications: Product status changed.				
PMV130ENEA v.1	20140313	Preliminary data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
11.1	Quality information	10
12	Package outline	11
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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